

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> 1N5624-TR

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of 1N5624-TR - DIODE AVALANCHE 200V 3A SOD64

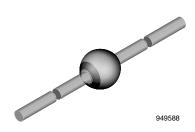
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1N5624, 1N5625, 1N5626, 1N5627

Vishay Semiconductors

Standard Avalanche Sinterglass Diode



MECHANICAL DATA

Case: SOD-64

Terminals: plated axial leads, solderable per

MIL-STD-750, method 2026

Polarity: color band denotes cathode end

Mounting position: any Weight: approx. 858 mg

FEATURES

- · Glass passivated junction
- · Hermetically sealed package
- · Controlled avalanche characteristics
- Low reverse current
- · High surge current loading
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

• Rectification diode, general purpose

ORDERING INFORMATION (Example)						
DEVICE NAME	E NAME ORDERING CODE TAPED UNITS MINIMUM ORDER QU					
1N5627	1N5627-TR	2500 per 10" tape and reel	12 500			
1N5627	1N5627-TAP	2500 per ammopack	12 500			

PARTS TABLE					
PART	TYPE DIFFERENTIATION	PACKAGE			
1N5624	$V_R = 200 \text{ V}; I_{F(AV)} = 3 \text{ A}$	SOD-64			
1N5625	V _R = 400 V; I _{F(AV)} = 3 A	SOD-64			
1N5626	V _R = 600 V; I _{F(AV)} = 3 A	SOD-64			
1N5627	$V_{R} = 800 \text{ V}; I_{E(AV)} = 3 \text{ A}$	SOD-64			

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT		
	See electrical characteristics	1N5624	$V_R = V_{RRM}$	200	V		
Reverse voltage = repetitive peak reverse		1N5625	$V_R = V_{RRM}$	400	V		
voltage		1N5626	$V_R = V_{RRM}$	600	V		
		1N5627	$V_R = V_{RRM}$	800	V		
Peak forward surge current	$t_p = 10 \text{ ms, half sinewave}$		I _{FSM}	100	Α		
Repetitive peak forward current			I _{FRM}	18	Α		
Average forward current			I _{F(AV)}	3	Α		
Pulse avalanche peak power	$t_p = 20 \mu s$, half sine wave, $T_i = 175 ^{\circ}C$		P _R	1000	W		
Pulse energy in avalanche mode, non repetitive (inductive load switch off)	$I_{(BR)R} = 1 \text{ A, } T_j = 175 ^{\circ}\text{C}$		E _R	20	mJ		
i ² *t-rating			i ² *t	40	A ² *s		
Junction and storage temperature range			$T_i = T_{stq}$	- 55 to + 175	°C		

MAXIMUM THERMAL RESISTANCE (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Junction ambient	I = 10 mm, T _L = constant	R _{thJA}	25	K/W	
Junction ambient	On PC board with spacing 25 mm	R _{thJA}	70	K/W	

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ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 3 A		V_{F}	-	-	1	V
Reverse current	$V_R = V_{RRM}$		I_{R}	-	0.1	1	μΑ
	$V_R = V_{RRM}$, $T_j = 100 ^{\circ}C$		I _R	-	5	10	μΑ
Breakdown voltage	$I_R = 100 \mu A, t_p/T = 0.01,$ $t_p = 0.3 \text{ ms}$		V _(BR)	-	-	1600	V
Diode capacitance	$V_R = 4 V, f = 1 MHz$		C_D	-	40	60	pF
Reverse recovery time	I _F = 0.5 A, I _R = 1 A, i _R = 0.25 A		t _{rr}	-	3.5	5	μs
	$I_F = 1 \text{ A}, \text{ dI/d}_t = 5 \text{ A/}\mu\text{s}, V_R = 50 \text{ V}$		t _{rr}	-	4.5	7.5	μs
Reverse recovery charge	$I_F = 1 \text{ A, } dI/d_t = 5 \text{ A/}\mu\text{s}$		Q _{rr}	-	8	12	μC

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

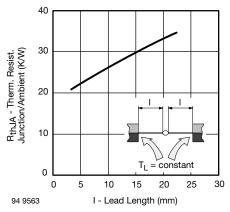


Fig. 1 - Max. Thermal Resistance vs. Lead Length

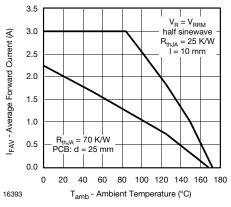


Fig. 3 - Max. Average Forward Current vs. Ambient Temperature

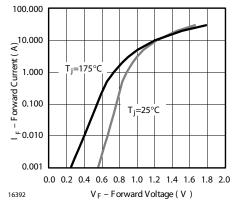


Fig. 2 - Forward Current vs. Forward Voltage

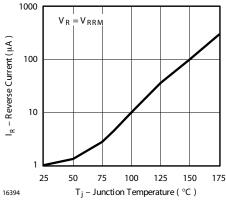


Fig. 4 - Reverse Current vs. Junction Temperature

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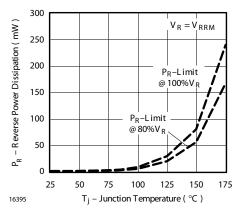


Fig. 5 - Max. Reverse Power Dissipation vs. Junction Temperature

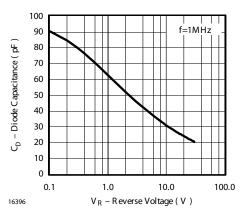
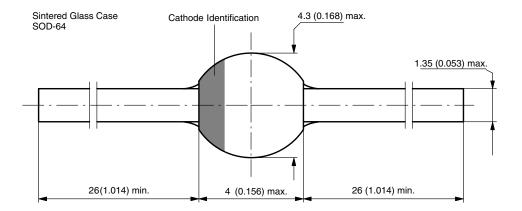


Fig. 6 - Diode Capacitance vs. Reverse Voltage

PACKAGE DIMENSIONS in millimeters (inches): SOD-64



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